

74HC238; 74HCT238

3-to-8 line decoder/demultiplexer

Rev. 03 — 16 July 2007

Product data sheet

1. General description

74HC238 and 74HCT238 are high-speed Si-gate CMOS devices and are pin compatible with Low-Power Schottky TTL (LSTTL).

The 74HC238/74HCT238 decoders accept three binary weighted address inputs (A0, A1, A2) and when enabled, provide 8 mutually exclusive active HIGH outputs (Y0 to Y7). The 74HC238/74HCT238 features three enable inputs: two active LOW ($\bar{E}1$ and $\bar{E}2$) and one active HIGH (E3). Every output will be LOW unless $\bar{E}1$ and $\bar{E}2$ are LOW and E3 is HIGH. This multiple enable function allows easy parallel expansion of the "238" to a 1-to-32 (5 lines to 32 lines) decoder with just four "238" ICs and one inverter. The "238" can be used as an eight output demultiplexer by using one of the active LOW enable inputs as the data input and the remaining enable inputs as strobes. Unused enable inputs must be permanently tied to their appropriate active HIGH or LOW state.

The 74HC238/74HCT238 is similar to the 74HC138/74HCT138 but has non-inverting outputs.

2. Features

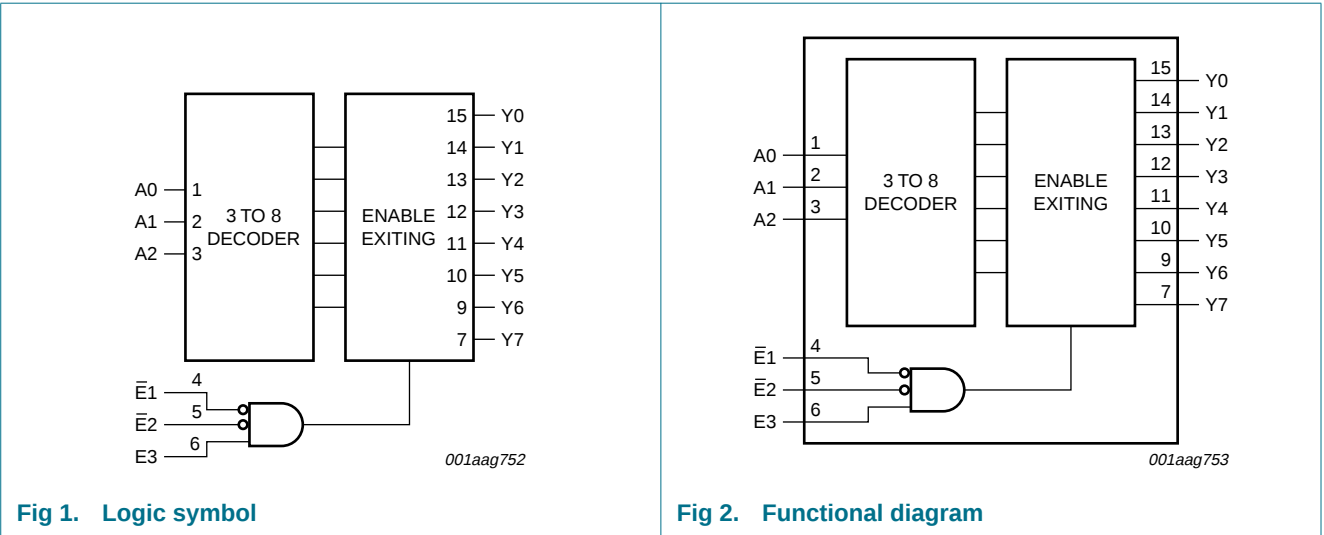
- Demultiplexing capability
- Multiple input enable for easy expansion
- Ideal for memory chip select decoding
- Active HIGH mutually exclusive outputs
- Multiple package options
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC238N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HC238D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC238DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HC238PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC238BQ	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT238N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT238D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT238DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT238PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT238BQ	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

4. Functional diagram



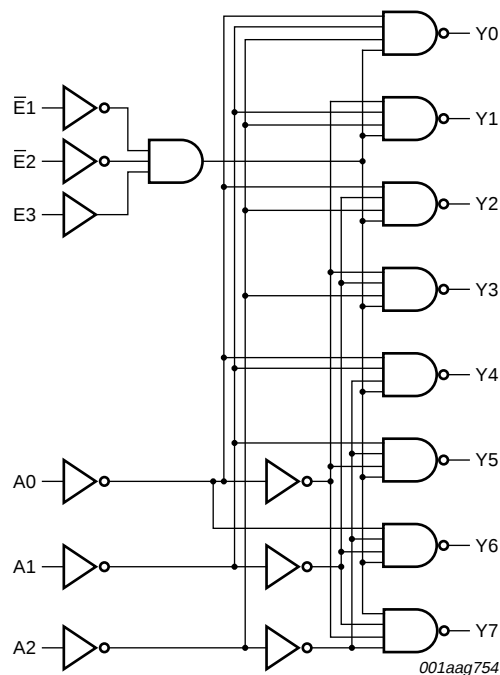


Fig 3. Logic diagram

5. Pinning information

5.1 Pinning

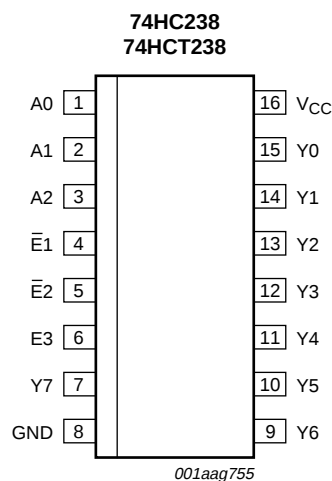
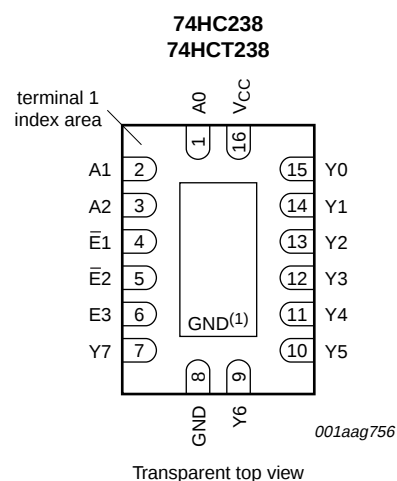


Fig 4. Pin configuration DIP16, SO16, (T)SSOP16



(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as supply pin or input

Fig 5. Pin configuration DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
A[0:2]	1, 2, 3	address input
$\bar{E}1$	4	enable input (active LOW)
$\bar{E}2$	5	enable input (active LOW)
E3	6	enable input (active HIGH)
Y[0:7]	15, 14, 13, 12, 11, 10, 9, 7	output (active HIGH)
GND	8	ground (0 V)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Inputs						Outputs							
$\bar{E}1$	$\bar{E}2$	E3	A0	A1	A2	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
H	X	X	X	X	X	L	L	L	L	L	L	L	L
X	H	X	X	X	X	L	L	L	L	L	L	L	L
X	X	L	X	X	X	L	L	L	L	L	L	L	L
L	L	H	L	L	L	H	L	L	L	L	L	L	L
L	L	H	H	L	L	L	H	L	L	L	L	L	L
L	L	H	L	H	L	L	L	H	L	L	L	L	L
L	L	H	H	H	L	L	L	L	H	L	L	L	L
L	L	H	L	L	H	L	L	L	L	H	L	L	L
L	L	H	H	L	H	L	L	L	L	L	H	L	L
L	L	H	L	H	H	L	L	L	L	L	L	H	L
L	L	H	H	H	H	L	L	L	L	L	L	L	H

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	±25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	DIP16 package	[2] -	750	mW
		SO16, SSOP16, TSSOP16 and DHVQFN16 packages	[3] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP16 packages: above 70 °C the value of P_{tot} derates linearly at 12 mW/K.

[3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC238			74HCT238			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC238										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = −5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT238										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = −20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V; $I_O = 0$ A	-	-	8.0	-	80	-	160	μ A
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V; $I_O = 0$ A								
		An inputs	-	70	252	-	315	-	343	μ A
		$\bar{E}1$, $\bar{E}2$ inputs	-	40	144	-	180	-	196	μ A
		E3 input	-	145	522	-	653	-	711	μ A
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristicsGND = 0 V; test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	

74HC238

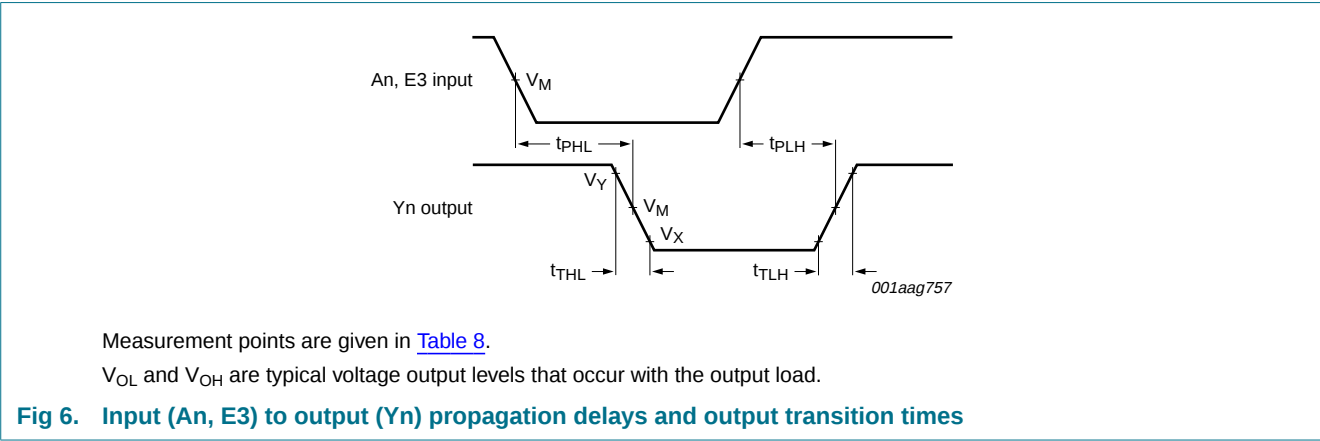
t_{pd}	propagation delay	An to Yn; see Figure 6	[1]						
		$V_{CC} = 2.0\text{ V}$	-	47	150	190	225	ns	
		$V_{CC} = 4.5\text{ V}$	-	17	30	38	45	ns	
		$V_{CC} = 5.0\text{ V}$; $C_L = 15\text{ pF}$	-	14	-	-	-	ns	
		$V_{CC} = 6.0\text{ V}$	-	14	26	33	38	ns	
		E3 to Yn; see Figure 6	[1]						
		$V_{CC} = 2.0\text{ V}$	-	52	160	200	240	ns	
		$V_{CC} = 4.5\text{ V}$	-	19	32	40	48	ns	
		$V_{CC} = 5.0\text{ V}$; $C_L = 15\text{ pF}$	-	16	-	-	-	ns	
		$V_{CC} = 6.0\text{ V}$	-	15	27	34	41	ns	
		$\bar{E}_n$ to Yn or see Figure 7	[1]						
		$V_{CC} = 2.0\text{ V}$	-	50	155	195	235	ns	
		$V_{CC} = 4.5\text{ V}$	-	18	31	39	47	ns	
		$V_{CC} = 5.0\text{ V}$; $C_L = 15\text{ pF}$	-	17	-	-	-	ns	
		$V_{CC} = 6.0\text{ V}$	-	14	26	33	40	ns	
t_t	transition time	see Figure 6 and Figure 7	[2]						
		$V_{CC} = 2.0\text{ V}$	-	19	75	95	110	ns	
		$V_{CC} = 4.5\text{ V}$	-	7	15	19	22	ns	
		$V_{CC} = 6.0\text{ V}$	-	6	13	16	19	ns	
C_{PD}	power dissipation capacitance	per package; $V_I = \text{GND to } V_{CC}$	[3]	-	72	-	-	-	pF

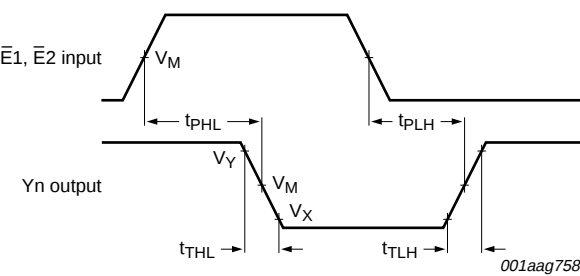
Table 7. Dynamic characteristics
GND = 0 V; test circuit see Figure 8.

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HCT238								
t _{pd}	propagation delay	An to Y _n ; see Figure 6	[1]					
		V _{CC} = 4.5 V	-	19	35	44	53	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	18	-	-	-	ns
		E3 to Y _n ; see Figure 6	[1]					
		V _{CC} = 4.5 V	-	20	37	46	56	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	20	-	-	-	ns
		Ē _n to Y _n or see Figure 7	[1]					
		V _{CC} = 4.5 V	-	20	35	44	53	ns
t _t	transition time	V _{CC} = 5.0 V; C _L = 15 pF	-	21	-	-	-	ns
		V _{CC} = 4.5 V; see Figure 6 and Figure 7	[2]	-	7	15	19	22
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} − 1.5 V	[3]	-	76	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH}.
- [2] t_t is the same as t_{THL} and t_{TLH}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
P_D = C_{PD} × V_{CC}² × f_i × N + Σ (C_L × V_{CC}² × f_o) where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
Σ (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms



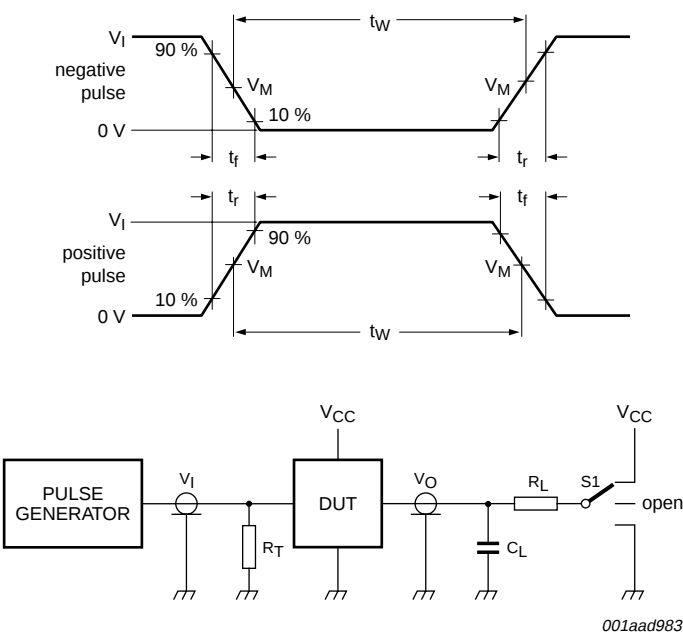


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Input ($\bar{E}1, \bar{E}2$) to output (Y_n) propagation delays and output transition times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC238	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
74HCT238	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$



Test data is given in [Table 9](#).
Definitions for test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = Load capacitance including jig and probe capacitance.
 R_L = Load resistance.
 $S1$ = Test selection switch

Fig 8. Load circuit for measuring switching times

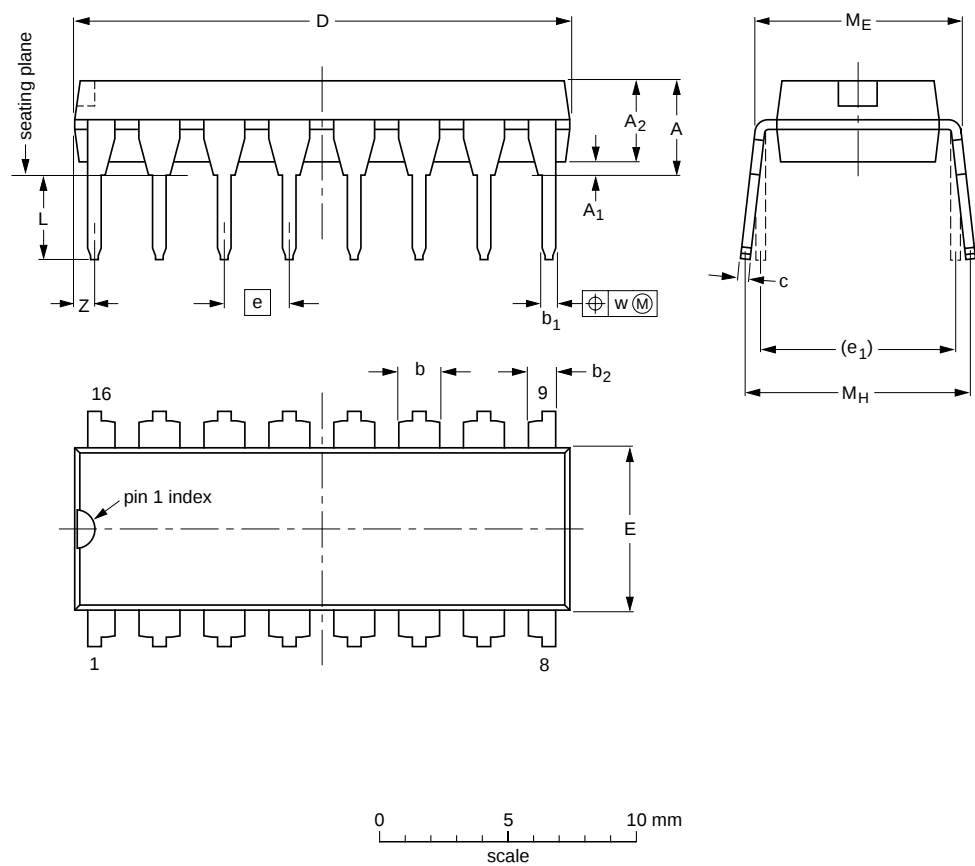
Table 9. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC238	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open
74HCT238	3 V	6 ns	15 pF, 50 pF	1 k Ω	open

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)																
UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

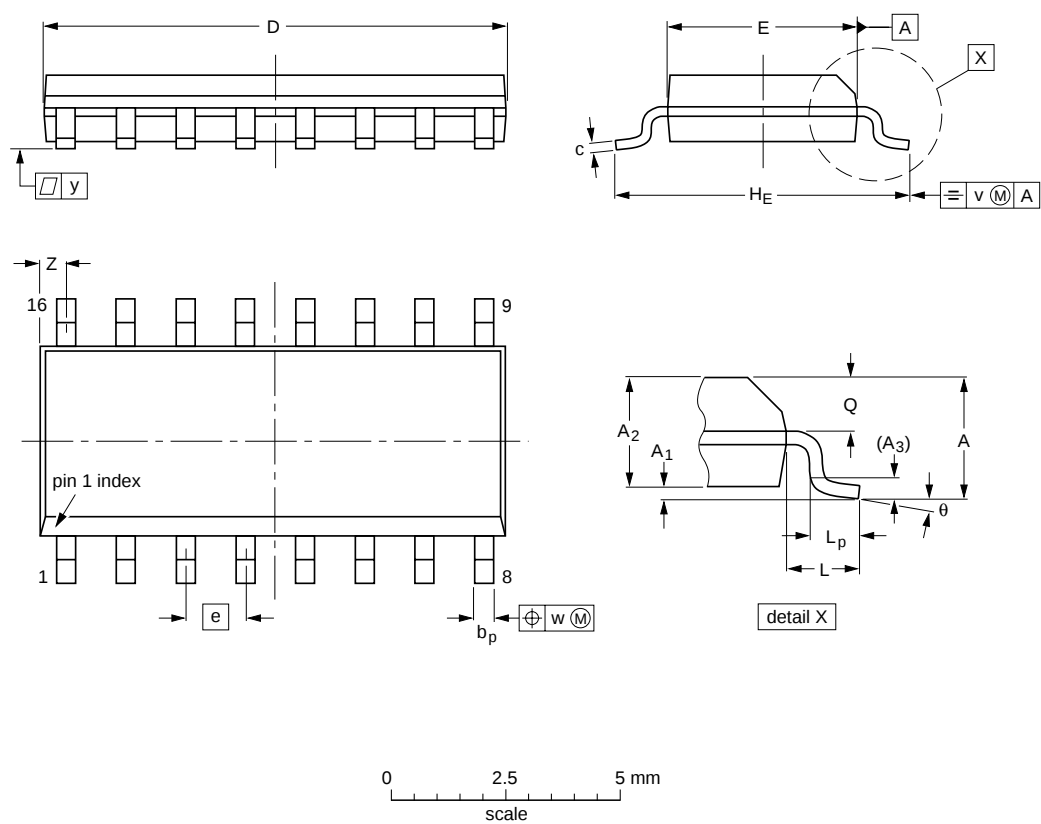
Note
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						95-01-14 03-02-13

Fig 9. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 10. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

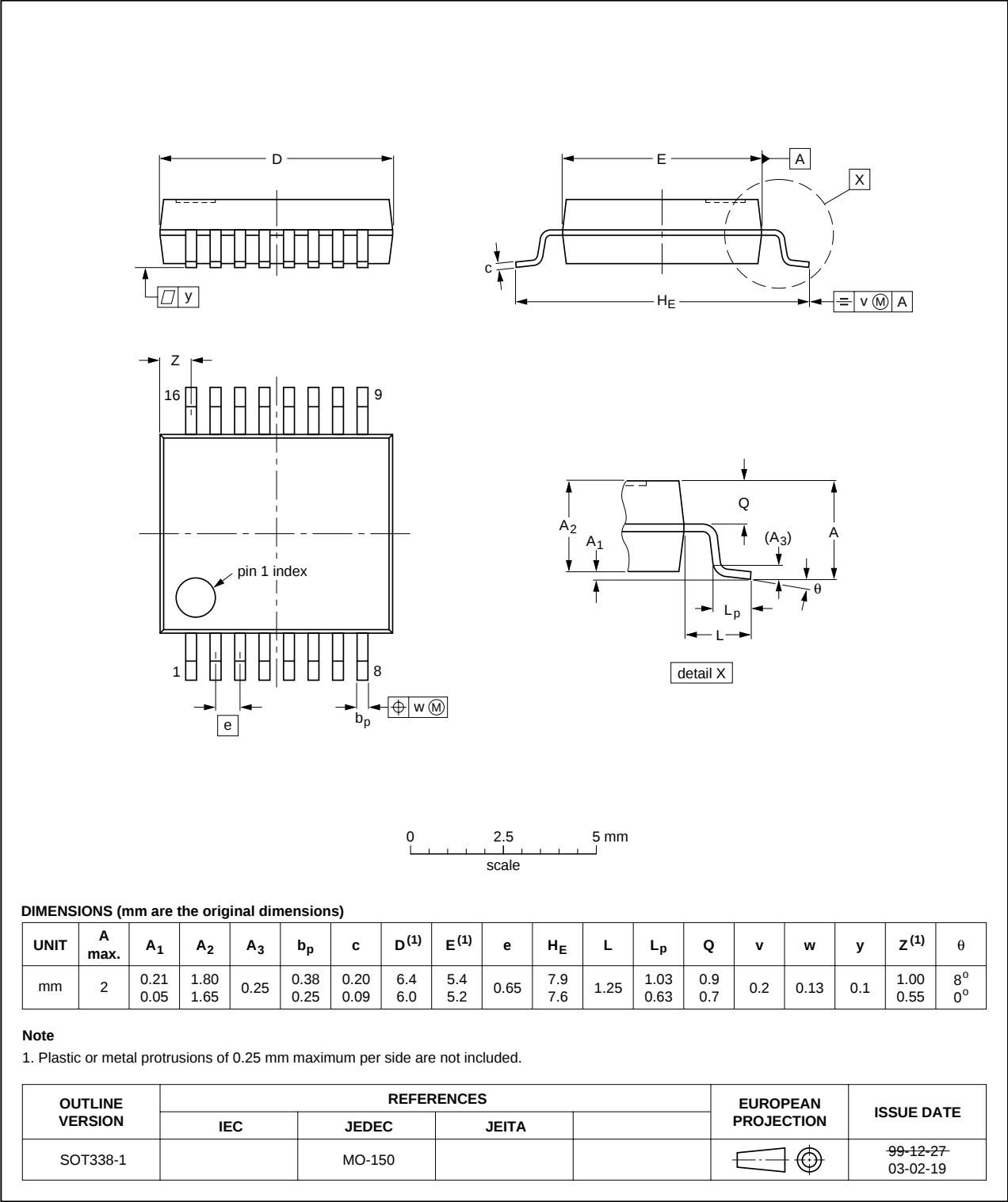


Fig 11. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

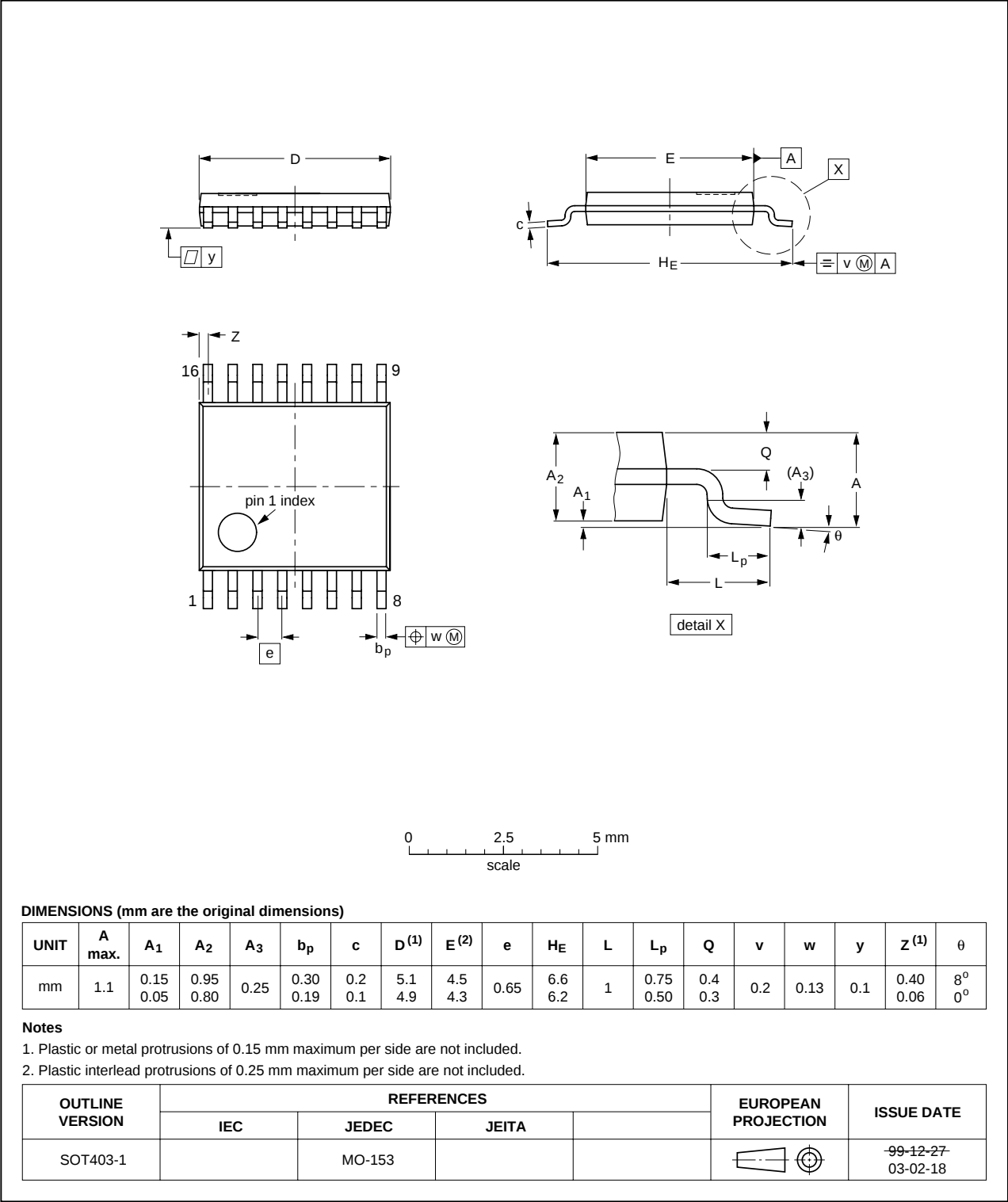


Fig 12. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

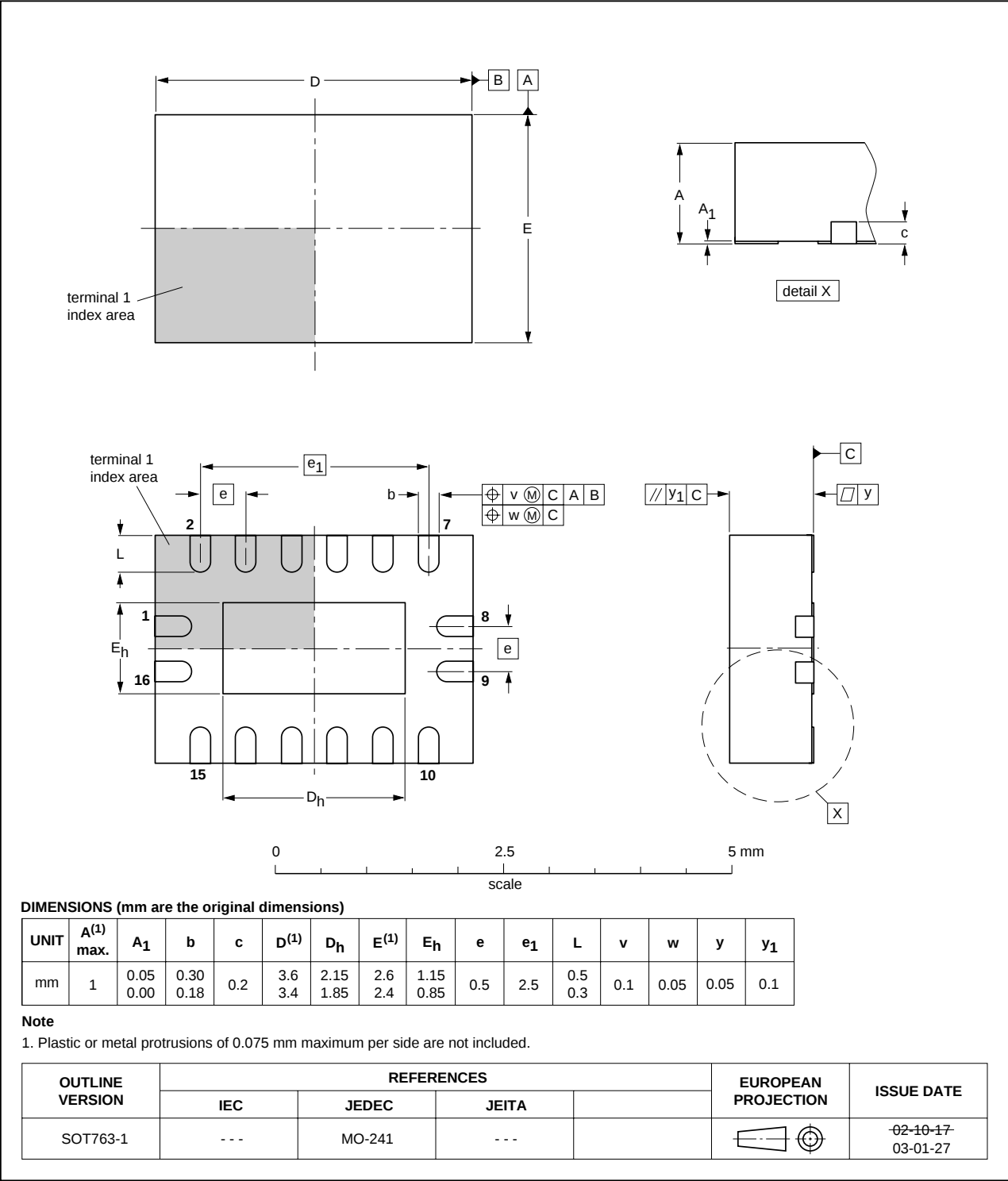


Fig 13. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT238_3	20070716	Product data sheet	-	74HC_HCT238_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Added type number 74HC238BQ and 74HCT238BQ (DHVQFN16 package)			
74HC_HCT238_CNV_2	19970828	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

15.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For additional information, please visit: <http://www.nxp.com>

For sales office addresses, send an email to: salesaddresses@nxp.com

17. Contents

1 General description 1

2 Features 1

3 Ordering information 2

4 Functional diagram 2

5 Pinning information 3

5.1 Pinning 3

5.2 Pin description 4

6 Functional description 4

7 Limiting values 5

8 Recommended operating conditions 5

9 Static characteristics 6

10 Dynamic characteristics 7

11 Waveforms 8

12 Package outline 11

13 Abbreviations 16

14 Revision history 16

15 Legal information 17

15.1 Data sheet status 17

15.2 Definitions 17

15.3 Disclaimers 17

15.4 Trademarks 17

16 Contact information 17

17 Contents 18



Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.